

LETTERS TO THE EDITOR

Syntheses and Characterization of Two Novel Inclusion Compounds: $\text{AlAsO}_4 \cdot 0.2(\text{CH}_3)_4\text{NOH} \cdot 0.3\text{H}_2\text{O}$ and $\text{GaAsO}_4 \cdot 0.2(\text{CH}_3)_4\text{NOH} \cdot 0.1\text{H}_2\text{O}$

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Two novel inclusion compounds similar to AlPO_4^{2-} or GaPO_4^{2-} were synthesized hydrothermally and characterized with X-ray powder diffraction, IR spectra, and thermal analyses. The chemical compositions were $\text{AlAsO}_4 \cdot 0.2(\text{CH}_3)_4\text{NOH} \cdot 0.3\text{H}_2\text{O}$ and $\text{GaAsO}_4 \cdot 0.2(\text{CH}_3)_4\text{NOH} \cdot 0.1\text{H}_2\text{O}$, respectively. © 1989 Academic Press, Inc.

Introduction

As molecular sieves, organic-amine-occluding AlPO_4^{2-} compounds (1) with open frameworks have been investigated widely. Recently, a new family of GaPO_4^{2-} (2-4) similar to AlPO_4^{2-} has proved very interesting. It is of considerable significance to clarify whether AlAsO_4^{2-} or GaAsO_4^{2-} inclusion compounds with open frameworks can be prepared since Al and Ga belong to Group IIIA and P and As belong to Group VA in the periodic table. Earlier, we reported a novel aluminoarsenate denoted AlAsO_4^{1-} occluding ethanolamine (5). In this letter, we describe the formation and characterization of two novel compounds (denoted AlAsO_4^{2-} and GaAsO_4^{1-} occluding tetramethylammonium hydroxide (TMAOH). GaAsO_4^{1-} is the first organic-amine-occluding galloarsenate reported so far.

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Experimental

Preparation of AlAsO_4^{2-} . Pyroarsenic acid, aluminum isopropylate, tetramethylammonium hydroxide, and water were mixed in the molar ratio 1.2 TMAOH : Al_2O_3 : 1.2 As_2O_5 : 40 H_2O . The mixture was stirred until homogeneous, sealed in a Teflon-lined autoclave, and heated at 200°C for 5 days. The crystalline product was separated from amorphous materials by an ultrasonic wave, washed with water, and dried at 100°C in air.

Preparation of GaAsO_4^{1-} . Metallic gallium was dissolved in nitric acid, precipitated as $\text{Ga}(\text{OH})_3$ with $\text{NH}_3 \cdot \text{H}_2\text{O}$, filtered, washed with water, and dried in air. $\text{Ga}(\text{OH})_3$ as prepared above, TMAOH, pyroarsenic acid, and water were mixed in the molar ratio 1.2 TMAOH : Ga_2O_3 : As_2O_5 : 36.0 H_2O . The subsequent procedure was the same as that described for AlAsO_4^{2-} except that the reaction temperature was 180°C.

Elemental analyses were performed on a P-240C element analyser, X-ray powder diffraction on a Rigaku 3DX diffractometer, IR spectra on a Nic-Nicolet 5DX spectrometer, and thermal analyses on a Rigaku thermobalance.

Results and Discussion

Under an optical microscope both AlAsO_4^{2-} and GaAsO_4^{1-} appear to be pure phases. The powder diffraction patterns (Fig. 1) reveal that they are new compounds with novel structures. The mole ratios of Al/As in AlAsO_4^{2-} and Ga/As in GaAsO_4^{1-} were measured by chemical analyses to be unity. Elemental analyses indicated that in AlAsO_4^{2-} , $C = 5.36\%$, $H = 1.79\%$, $N = 1.79\%$, and in GaAsO_4^{1-} , $C = 3.83\%$, $H = 1.08\%$, $N = 1.51\%$. The empirical formulae of AlAsO_4^{2-} and GaAsO_4^{1-} derived from these analyses were $\text{AlAsO}_4 \cdot 0.2(\text{CH}_3)_4\text{NOH} \cdot 0.3\text{H}_2\text{O}$ and $\text{GaAsO}_4 \cdot 0.2(\text{CH}_3)_4\text{NOH} \cdot 0.1\text{H}_2\text{O}$, respectively. For synthesis of AlAsO_4^{2-} , the favorable molar ratios were $\text{As}_2\text{O}_5/\text{Al}_2\text{O}_3 = 1.0\text{--}1.3$, $\text{TMAOH}/\text{Al}_2\text{O}_3 = 1.0\text{--}1.5$, $\text{H}_2\text{O}/$

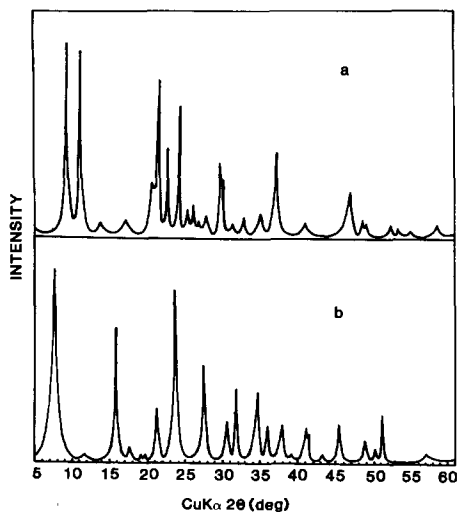


FIG. 1. X-ray powder diffraction patterns of AlAsO_4^{2-} (a) and GaAsO_4^{1-} (b).

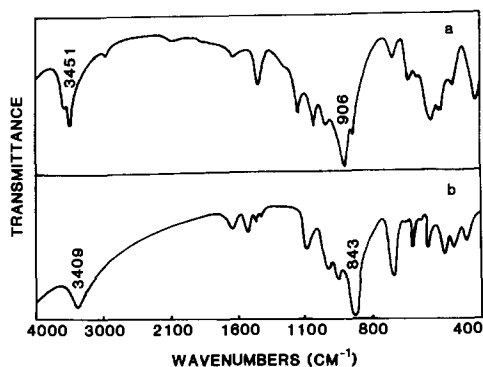


FIG. 2. IR spectra of AlAsO_4^{2-} (a) and GaAsO_4^{1-} (b).

$\text{Al}_2\text{O}_3 = 35\text{--}50$. $\text{As}_2\text{O}_5/\text{Al}_2\text{O}_3$ larger than 1.5 readily resulted in dense phases of AlAsO_4 . The ranges suitable for synthesis of GaAsO_4^{1-} were $\text{As}_2\text{O}_5/\text{Ga}_2\text{O}_3 = 1.0\text{--}1.2$, $\text{TMAOH}/\text{Ga}_2\text{O}_3 = 1.2\text{--}1.6$, and $\text{H}_2\text{O}/\text{Ga}_2\text{O}_3 = 30\text{--}45$. Reaction temperatures higher than 200°C led to formation of α -quartz-type GaAsO_4 . We have also tried, but failed, to synthesize AlAsO_4 and GaAsO_4 inclusion compounds using other larger quaternary ammonium hydroxides such as tetraethylammonium, tetrapropylammonium, and tetrabutylammonium hydroxides.

The IR spectrum of AlAsO_4^{2-} (Fig. 2) shows a main absorption at 906 cm^{-1} corresponding to asymmetric stretching vibrations of TO_n ($T = \text{Al or As}$, $n = 4\text{--}6$) coordination polyhedra (6). The wavenumber is 45 cm^{-1} smaller than that of α -quartz-type AlAsO_4 . The absorption at 3451 cm^{-1} is assigned to the vibrations of O-H bonds. The DTA curve of AlAsO_4^{2-} (Fig. 3) has small endothermic peaks between 400 and 460°C and pronounced exothermic peaks between 600 and 650°C . In these two temperature ranges the TGA curve shows corresponding weight losses. On the basis of other work (7), the low-temperature thermal effect is assigned to the pyrolysis of occluded TMAOH and the high-temperature one to its oxidative decomposition.

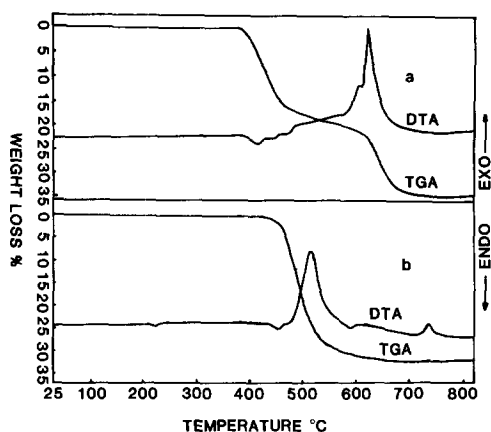


FIG. 3. TGA-DTA in air of AlAsO_4^{2-} (a) and GaAsO_4^{1-} (b).

The TO_n ($T = \text{Ga}$ or As , $n = 4-6$) IR absorption of GaAsO_4^{-1} (Fig. 2) is at 843 cm^{-1} , 42 cm^{-1} smaller than that of α -quartz-type GaAsO_4 . The O-H absorption is around 3409 cm^{-1} . Differing from that of AlAsO_4^{-2} , the TGA curve of GaAsO_4^{-1} (Fig. 3) shows

only one evident weight loss from 420 to 600°C . However, its DTA curve shows a small endothermic effect near 450°C in addition to a pronounced exothermic effect around 510°C . This phenomenon suggests that the oxidative decomposition of TMAOH begins before the end of its pyrolysis.

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